| | Hits | Search Text | DBs | Time Stamp |
|---|------|---------------|---|---------------------|
| 1 | 202 | 257/4.ccls. | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | 2005/09/30 17:58 |
| 2 | 318 | 257/183.ccls. | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | 2005/09/30 17:58 |
| 3 | 1131 | 257/197.ccls. | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | 2005/09/30 17:59 |
| 4 | 723 | 257/378.ccls. | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | 2005/09/30 17:59 |
| 5 | 1166 | 257/565.ccls. | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | 2005/09/30 17:59 |
| 6 | 214 | 257/578.ccls. | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | 2005/09/30 17:59 |
| 7 | 499 | 438/309.ccls. | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | 2005/09/30 17:59 |
| 8 | 323 | 438/312.ccls. | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | 2005/09/30 17:59 |
| 9 | 98 | 438/342.ccls. | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | 2005/09/30 18:18 |

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|----|-------|---|---|---------------------|
| 10 | 66821 | bipolar adj (transistor | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | 2005/09/30 18:00 |
| 11 | 5227 | bipolar adj (transistor transistors) near3 | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | 2005/09/30 18:00 |
| 12 | 498 | transistors) near3 heterojunction and | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | 2005/09/30 18:04 |
| 13 | 6 | ("5729033" "6605519" "6376867") pp | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | 2005/09/30 18:03 |
| 14 | 95 | heterojunction and collector and base and emitter and can and metal | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | 2005/09/30 18:09 |
| 15 | 2 | "20040224463" | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | 2005/09/30 18:06 |
| 16 | 25 | heterojunction and collector and base and emitter and cap and metal | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | 2005/09/30 18:10 |
| 17 | 7 | "5804487" "6310368" "6376867" "6406965" | US-PGPUB; USPAT; USOCR | 2005/09/30 18:12 |

| | Hits | Search Text | DBs | Time Stamp |
|----|------|-------------------|---|---------------------|
| 18 | 46 | 438/315.ccls. | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | 2005/09/30 18:14 |
| 19 | 43 | 438/334.ccls. | 19: P() + 11 P() + | 2005/09/30 18:17 |
| 20 | 5 | 438/342.ccls. and | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | 2005/09/30 18:19 |

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Inventor Information for 10/826787

| Inventor Name | City | State/Country | | | |
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| DEBRABANDER, GREGORY N. | SAN JOSE | CALIFORNIA | | | |
| Appln Info Contents . Petition Info Atty/Agent Info Continuity Data Foreign D | | | | | |
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Inventor Name Search Result

Your Search was:

Last Name = MCHUGO

First Name = SCOTT

| Application# | Patent# | Status | Date Filed | Title | Inventor Name |
|-----------------|---------------|--------|------------|--|---------------------|
| <u>60701831</u> | Not Issued | 20 | | Metal and polymer balloon material for catheters | MCHUGO, SCOTT |
| 10435230 | 6806129 | 150 | 05/09/2003 | SELF-ALIGNED PROCESS USING INDIUM GALLIUM ARSENIDE ETCHING TO FORM REENTRY FEATURE IN HETEROJUNCTION BIPOLAR TRANSISTORS | MCHUGO, SCOTT A. |
| 10826787 | Not Issued | 30 | 04/16/2004 | Self-aligned process using indium gallium arsenide etching to form reentry feature in heterojunction bipolar transistors | MCHUGO, SCOTT A. |
| 10892983 | Not Issued | 30 | 07/15/2004 | VCSEL having an air gap and protective coating | MCHUGO, SCOTT A. |

Inventor Search Completed: No Records to Display.

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Last Name = DEBRABANDER

First Name = GREGORY

| Application# | Patent# | Status | Date Filed | Title | Inventor Name |
|--------------|---------------|--------|------------|--|----------------------------|
| 10361092 | 6862309 | 150 | 02/06/2003 | PASSIVATION SCHEME FOR OXIDE VERTICAL CAVITY SURFACE- EMITTING LASER | DEBRABANDER, GREGORY N. |
| 10387621 | Not Issued | 71 | 03/12/2003 | Detecting pinholes in vertical cavity surface-emitting laser passivation | DEBRABANDER, GREGORY N. |
| 10435230 | 6806129 | 150 | 05/09/2003 | SELF-ALIGNED PROCESS USING INDIUM GALLIUM ARSENIDE ETCHING TO FORM REENTRY FEATURE IN HETEROJUNCTION BIPOLAR TRANSISTORS | DEBRABANDER, GREGORY N. |
| 10826787 | Not Issued | 30 | 04/16/2004 | Self-aligned process using indium gallium arsenide etching to form reentry feature in heterojunction bipolar transistors | DEBRABANDER, GREGORY N. |
| 11096397 | Not Issued | 30 | 03/31/2005 | Detecting pinholes in vertical cavity surface-emitting laser passivation | DEBRABANDER, GREGORY N. |

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